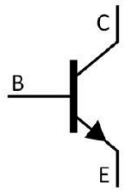
TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

P_C I_C h_{FE} 3CG9012

High P_C and I_C, excellent h_{FE} linearity, complementary pair with3DG 9012.

Amplifier of portable radios in class B push-pull operation.

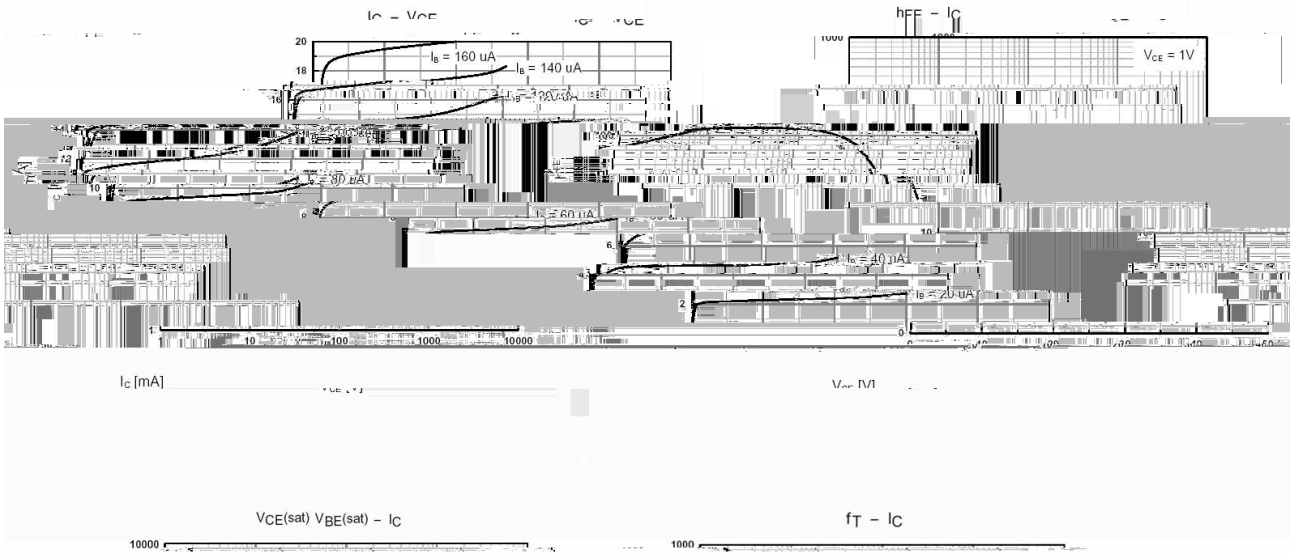


PIN1 Base PIN 2 Collector PIN 3 Emitter

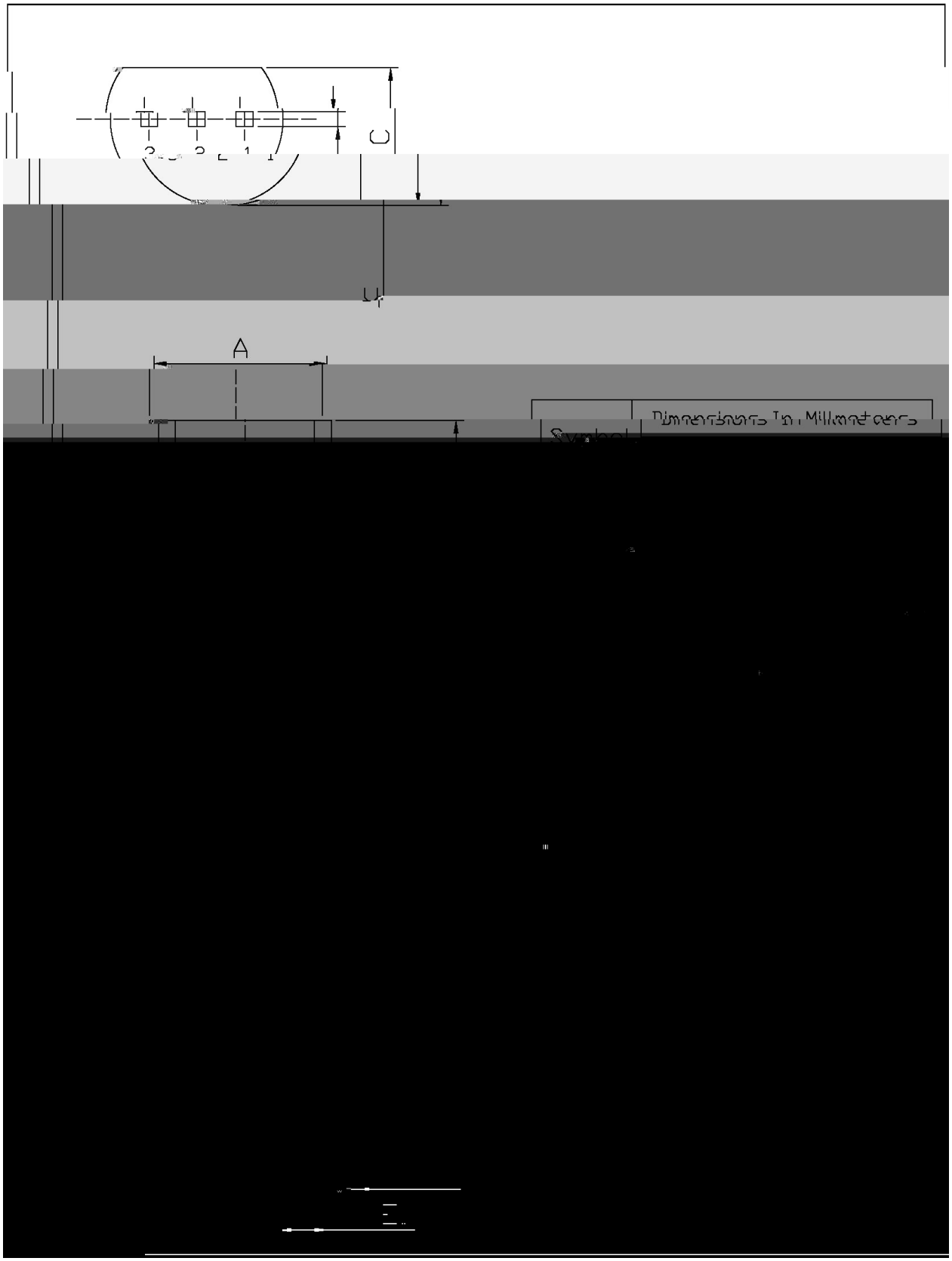
h_{FE} Classifications Symbol	D	E	F	G	H	I
h_{FE} Range	64~91	78~112	96~135	112~166	144~202	188~276

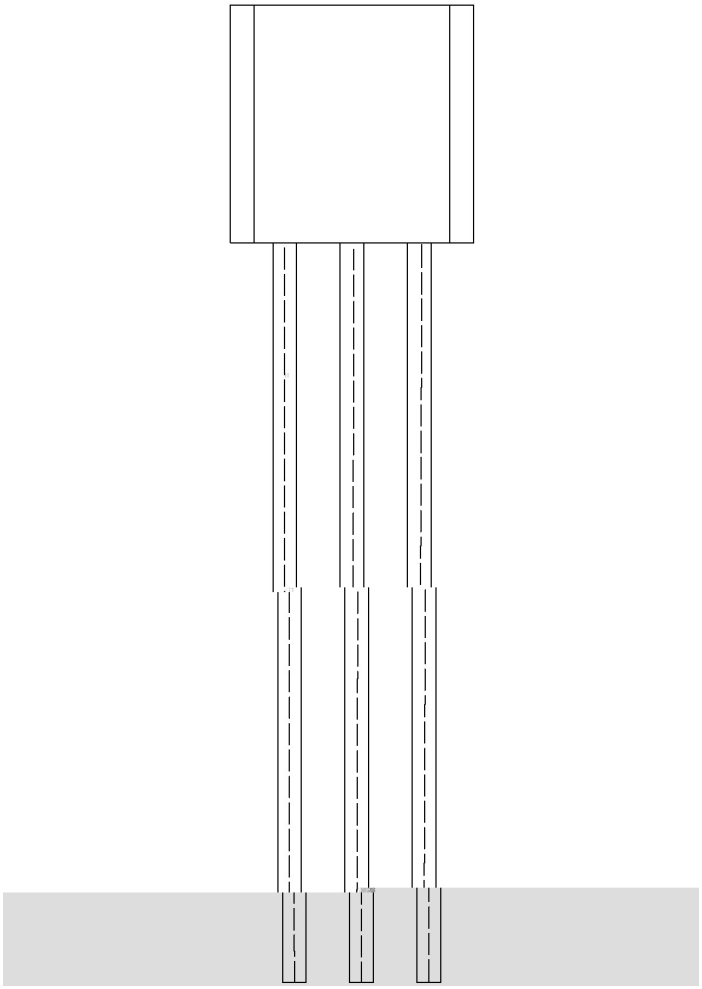
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	500	mA
Base Current - Continuous	I_B	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=25V I_E=0			0.1	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=3.0V I_C=0			0.1	A
DC Current Gain	$h_{FE(1)}$	$V_=$ 3 . 0 V 0 T D 5 T m 6 4 0 . 4 7 9 9 8 - 5				


I_B = 160 uA
I_B = 140 uA
I_B = 120 uA
I_B = 100 uA
I_B = 80 uA
I_B = 60 uA
I_B = 40 uA
I_B = 20 uA
V_{CE} = 1V
I_C [mA]
$V_{CE(sat)}$ $V_{BE(sat)}$ – I_C
f_T – I_C

TO-92 Unit: mm

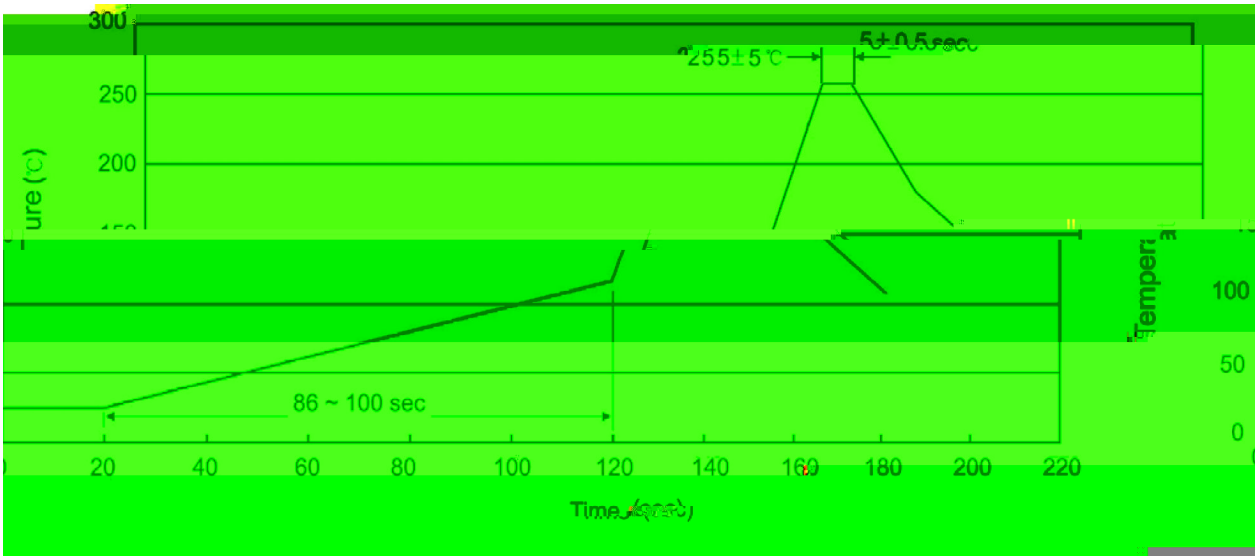




9013

D: h_{FE}

****



					Note:
1	25	150	60	90sec;	1.Preheating:25~150